

[ABSTRACT]

A method of forming a resist pattern, which includes a step of forming a resist film having a film thickness of 7 μm or more on a supporting body using a resist composition, a step of exposing the resist film to light, and a step of developing the exposed resist film to form a resist pattern, in which as the resist composition, a base material component whose solubility in a developing solution is changed due to an action of an acid and an acid generator composed of a compound represented by General Formula (b1-1) are contained (In Formula (b1-1), Rb^1 represents an aryl group. Rb^2 and Rb^3 are an aliphatic hydrocarbon group. $\text{R}^{\text{b}2}$ and $\text{R}^{\text{b}3}$ may be bonded to each other to form a ring structure. $\text{L}^{\text{b}1}$, $\text{L}^{\text{b}2}$, and $\text{L}^{\text{b}3}$ are a divalent linking group or a single bond. X^- represents a counter anion.).

